

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity




Applications

- LED lighting
- Telecom
- Adapter
- Sever
- Solar/UPS

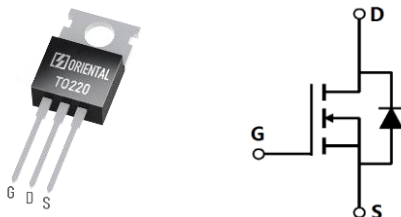
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	250	V
$I_{D, pulse}$	78	A
$R_{DS(ON), max @ V_{GS}=10V}$	60	m Ω
Q_g	18	nC

Marking Information

Product Name	Package	Marking
OSG25R060PF	TO220	OSG25R060P

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	250	V
Gate-source voltage (static)	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	26	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		16	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	78	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	26	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, pulse}$	78	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	57	W
Single pulsed avalanche energy ⁴⁾	E_{AS}	65	mJ
Reverse diode dv/dt	dv/dt	10	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	2.2	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	250			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	3.0		5.0	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		46	60	m Ω	$V_{GS}=10\text{ V}, I_D=13\text{ A}$
			92			$V_{GS}=10\text{ V}, I_D=13\text{ A}, T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=250\text{ V}, V_{GS}=0\text{ V}$
Gate resistance	R_G		4.6		Ω	$f=1\text{ MHz}, \text{Open drain}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1115		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		55		pF	
Reverse transfer capacitance	C_{rss}		2.2		pF	
Turn-on delay time	$t_{d(on)}$		12		ns	$V_{GS}=10\text{ V}$, $V_{DS}=100\text{ V}$, $R_G=2\ \Omega$, $I_D=13\text{ A}$
Rise time	t_r		2		ns	
Turn-off delay time	$t_{d(off)}$		24		ns	
Fall time	t_f		2		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		18		nC	$V_{GS}=10\text{ V}$, $V_{DS}=100\text{ V}$, $I_D=13\text{ A}$
Gate-source charge	Q_{gs}		6		nC	
Gate-drain charge	Q_{gd}		5		nC	
Gate plateau voltage	$V_{plateau}$		6.1		V	

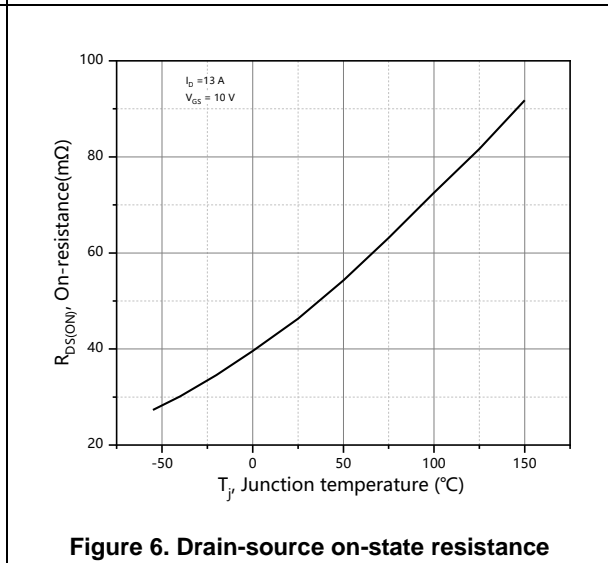
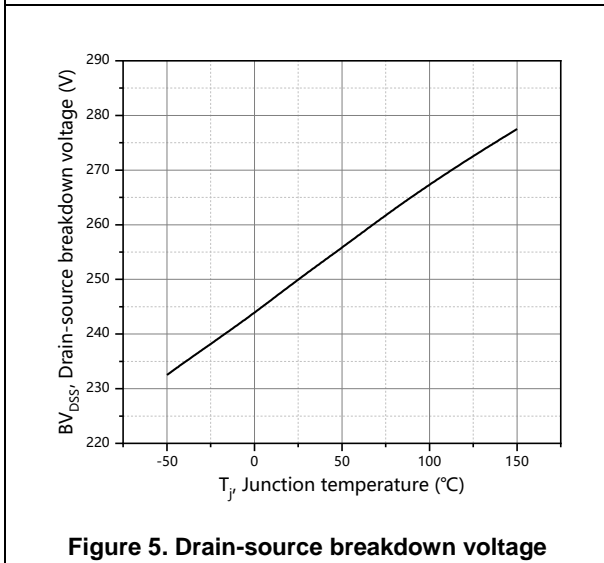
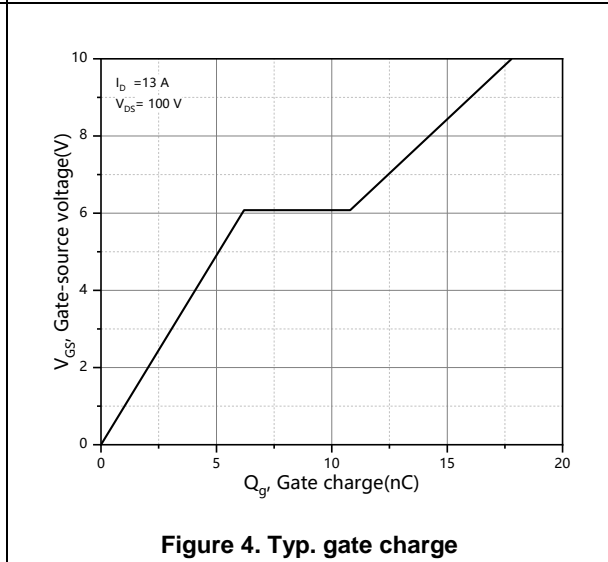
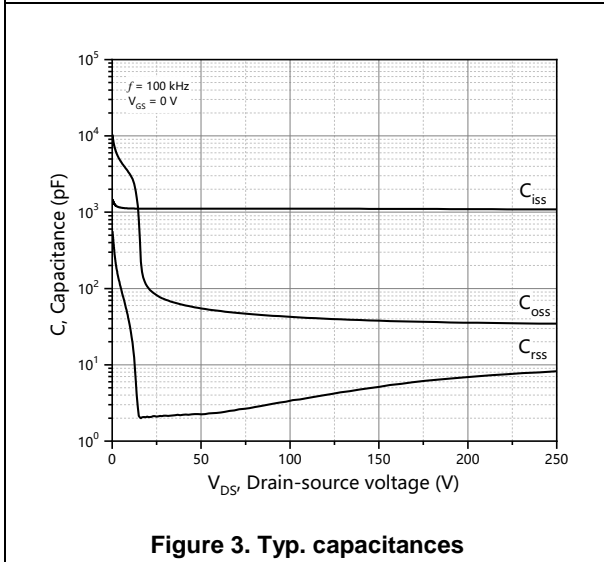
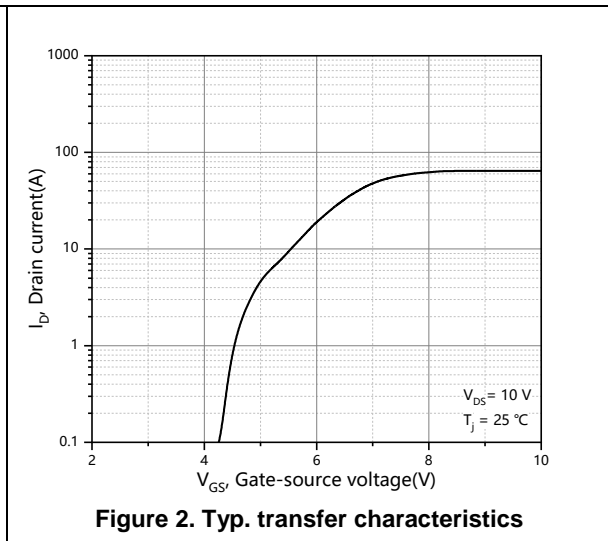
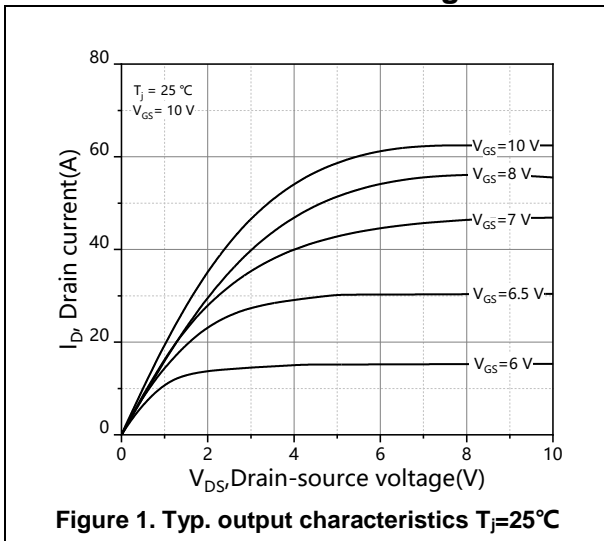
Body Diode Characteristics

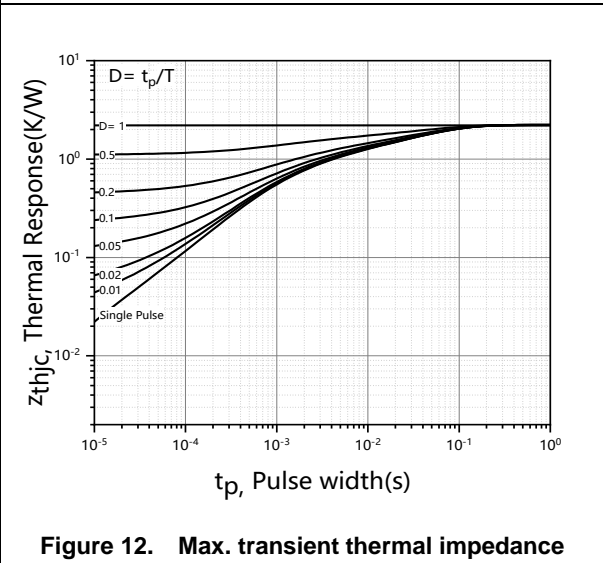
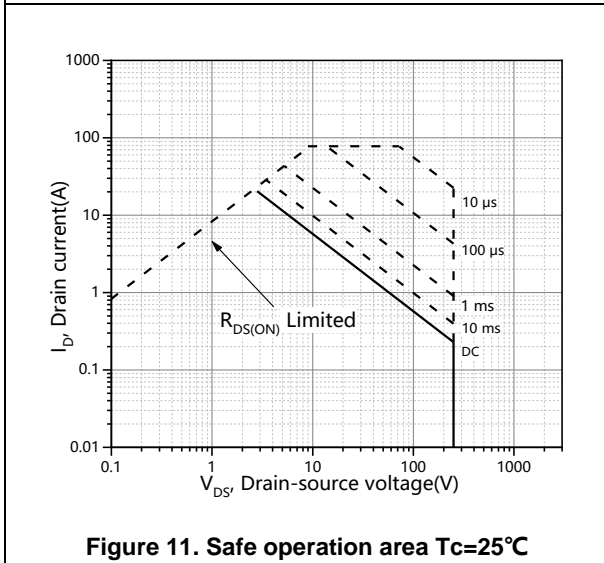
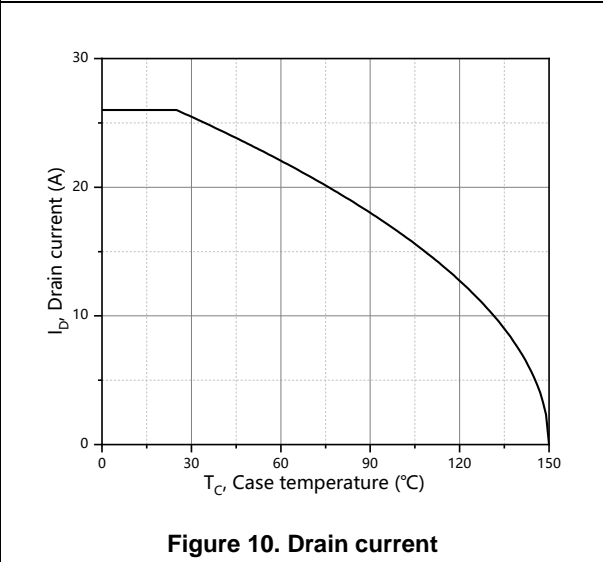
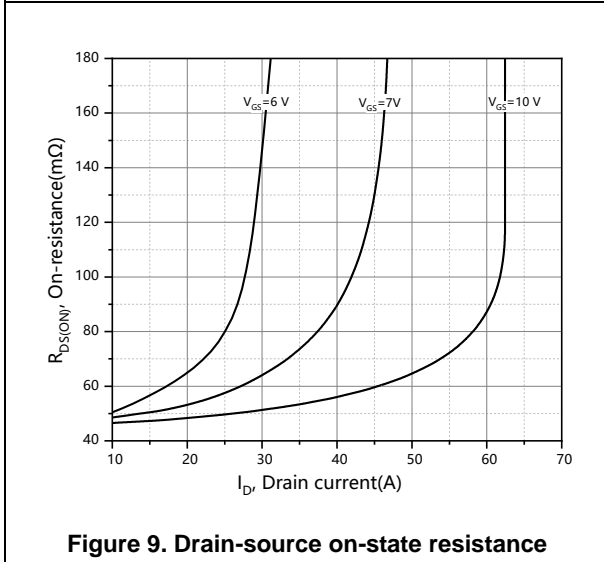
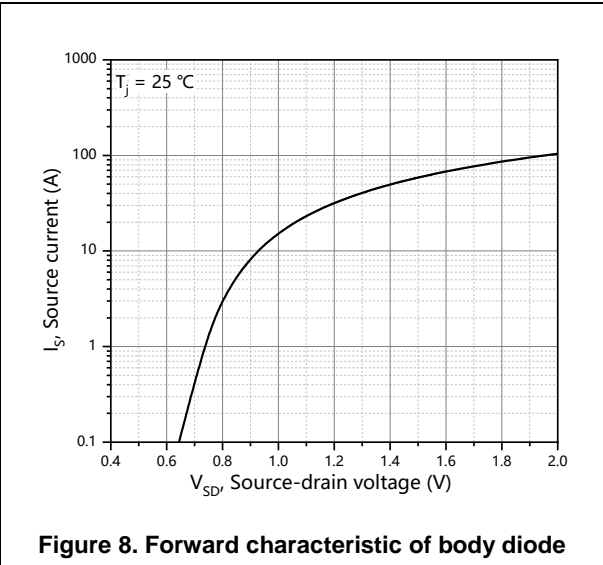
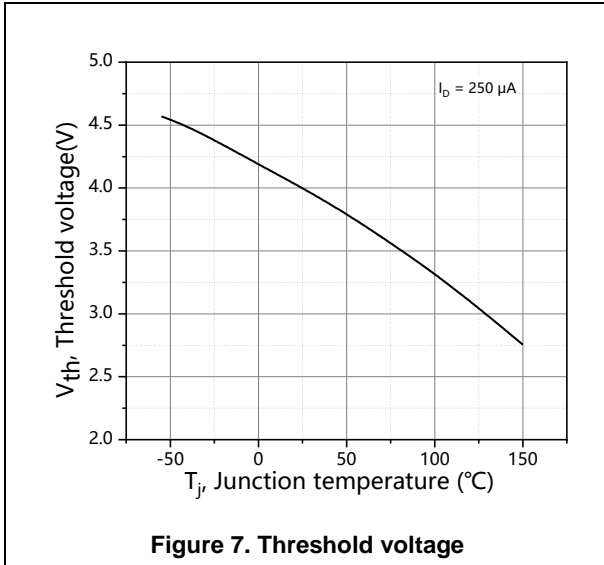
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=26\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		69		ns	$V_R=100\text{ V}$, $I_S=13\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		0.2		μC	
Peak reverse recovery current	I_{rrm}		4.8		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=80\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams





Test circuits and waveforms



Figure 1. Gate charge test circuit & waveform



Figure 2. Switching time test circuit & waveforms

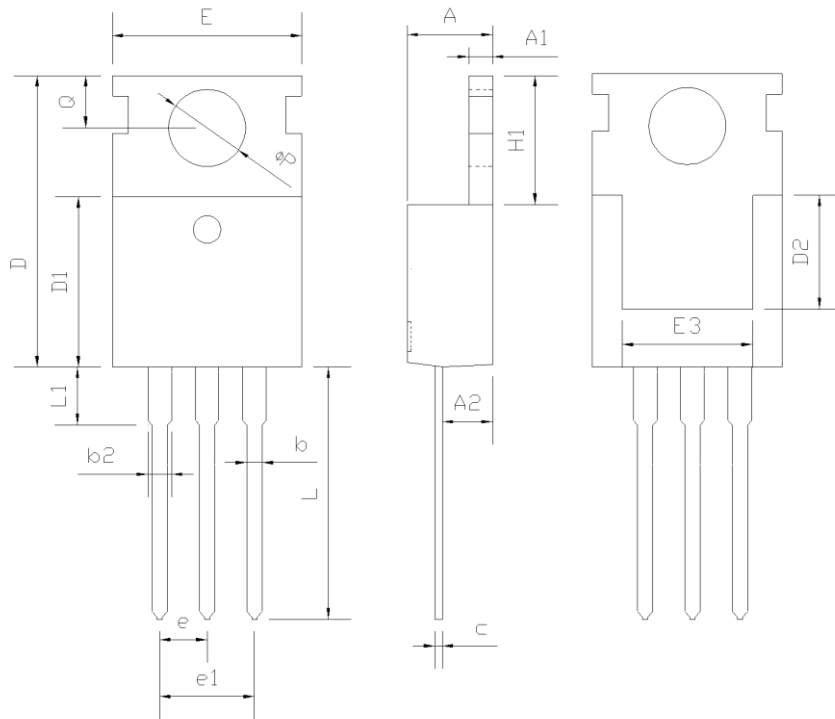


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms



Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00

Version: TO220-P package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220-P	50	20	1000	6	6000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG25R060PF	TO220	yes	yes	yes

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